

FORMULATIONS AND METHOD FOR POST-CMP CLEANING  
ABSTRACT OF THE DISCLOSURE

The present invention is a method of cleaning to removal residue in  
5 semiconductor manufacturing processing, comprising contacting a surface to be cleaned  
with an aqueous formulation having a polymer selected from the group consisting of  
acrylamido-methyl-propane sulfonate) polymers, acrylic acid-2-acrylamido-2-  
methylpropane sulfonic acid copolymer and mixtures thereof and a quaternary  
ammonium hydroxide having greater than 4 carbon atoms or choline hydroxide with a  
10 non-acetylinic surfactant.

The present invention is also a post-CMP cleaning formulation having the  
components set forth in the method above.